Saien Xie

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

26 26 2,504 12 g-index h-index citations papers 26 3,033 14.3 4.91 avg, IF L-index ext. citations ext. papers

#	Paper	IF	Citations
26	Resist-Free Lithography for Monolayer Transition Metal Dichalcogenides Nano Letters, 2022,	11.5	3
25	Strong interlayer interactions in bilayer and trilayer moir uperlattices Science Advances, 2022, 8, eabk	194.3	1
24	Utilizing complex oxide substrates to control carrier concentration in large-area monolayer MoS2 films. <i>Applied Physics Letters</i> , 2021 , 118, 093103	3.4	7
23	Local Electronic Properties of Coherent Single-Layer WS/WSe Lateral Heterostructures. <i>Nano Letters</i> , 2021 , 21, 2363-2369	11.5	4
22	Interfacial Electron-Phonon Coupling Constants Extracted from Intrinsic Replica Bands in Monolayer FeSe/SrTiO_{3}. <i>Physical Review Letters</i> , 2021 , 127, 016803	7.4	4
21	Impact of 2D-3D Heterointerface on Remote Epitaxial Interaction through Graphene. <i>ACS Nano</i> , 2021 , 15, 10587-10596	16.7	15
20	Tuning Electrical Conductance of MoS Monolayers through Substitutional Doping. <i>Nano Letters</i> , 2020 , 20, 4095-4101	11.5	59
19	Evidence for the Dominance of Carrier-Induced Band Gap Renormalization over Biexciton Formation in Cryogenic Ultrafast Experiments on MoS Monolayers. <i>Journal of Physical Chemistry Letters</i> , 2020 , 11, 2658-2666	6.4	11
18	Imaging Polarity in Two Dimensional Materials by Breaking Friedel's Law. <i>Ultramicroscopy</i> , 2020 , 215, 113019	3.1	8
17	Heterogeneous integration of single-crystalline complex-oxide membranes. <i>Nature</i> , 2020 , 578, 75-81	50.4	107
16	Uncovering Atomic and Nano-scale Deformations in Two-dimensional Lateral Heterojunctions. <i>Microscopy and Microanalysis</i> , 2020 , 26, 1630-1631	0.5	
15	Coherent, atomically thin transition-metal dichalcogenide superlattices with engineered strain. <i>Science</i> , 2018 , 359, 1131-1136	33.3	170
14	Electron ptychography of 2D materials to deep sub-figstrfh resolution. <i>Nature</i> , 2018 , 559, 343-349	50.4	269
13	Real-space Demonstration of 0.4 Angstrom Resolution at 80 keV via Electron Ptychography with a High Dynamic Range Pixel Array Detector. <i>Microscopy and Microanalysis</i> , 2018 , 24, 194-195	0.5	
12	Mapping Strain and Relaxation in 2D Heterojunctions with Sub-picometer Precision. <i>Microscopy and Microanalysis</i> , 2018 , 24, 1588-1589	0.5	
11	Strain Mapping of Two-Dimensional Heterostructures with Subpicometer Precision. <i>Nano Letters</i> , 2018 , 18, 3746-3751	11.5	50
10	Absence of a Band Gap at the Interface of a Metal and Highly Doped Monolayer MoS. <i>Nano Letters</i> , 2017 , 17, 5962-5968	11.5	27

LIST OF PUBLICATIONS

9	Layer-by-layer assembly of two-dimensional materials into wafer-scale heterostructures. <i>Nature</i> , 2017 , 550, 229-233	50.4	305
8	Picometer-Precision Strain Mapping of Two-Dimensional Heterostructures using an Electron Microscope Pixel Array Detector (EMPAD). <i>Microscopy and Microanalysis</i> , 2017 , 23, 1712-1713	0.5	
7	Breaking Friedel Law in Polar Two Dimensional Materials. <i>Microscopy and Microanalysis</i> , 2017 , 23, 1738	-107539	1
6	Electron Diffraction from a Single Atom and Optimal Signal Detection. <i>Microscopy and Microanalysis</i> , 2016 , 22, 846-847	0.5	3
5	Atomically Thin Ohmic Edge Contacts Between Two-Dimensional Materials. ACS Nano, 2016, 10, 6392-9	16.7	144
4	Strain Accommodation and Coherency in Laterally-Stitched WSe 2 /WS 2 Junctions. <i>Microscopy and Microanalysis</i> , 2016 , 22, 870-871	0.5	5
3	Atomic-Scale Spectroscopy of Gated Monolayer MoS2. <i>Nano Letters</i> , 2016 , 16, 3148-54	11.5	23
2	Long-Lived Hole Spin/Valley Polarization Probed by Kerr Rotation in Monolayer WSe2. <i>Nano Letters</i> , 2016 , 16, 5010-4	11.5	64
1	High-mobility three-atom-thick semiconducting films with wafer-scale homogeneity. <i>Nature</i> , 2015 , 520, 656-60	50.4	1224